

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI MLN1030SS** is Designed for Class A Linear Applications up to 1.0 GHz.

FEATURES:

- Class A Operation
- $P_G = 10$ dB at 1.0 W/1.0 GHz
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	10 A
V_{CB}	60 V
V_{CE}	35 V
P_{DISS}	140 W @ $T_C = 25^\circ C$
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	20 °C/W

PACKAGE STYLE .205 4L STUD

DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.976 / 24.800	1.000 / 25.4000
B	.976 / 24.800	1.000 / 25.4000
C	.028 / 0.700	.031 / 0.800
D	.138 / 3.500	
E	.161 / 4.100	.196 / 5.000
F	.098 / 2.500	.110 / 2.800
G	.200 / 5.100	.208 / 5.300
H	.004 / 0.100	.006 / 0.150
I	.425 / 10.800	.465 / 11.800
J	.200 / 5.100	2.05 / 5.200

ORDER CODE: ASI10625

CHARACTERISTICS $T_C = 25^\circ C$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	$I_C = 50$ mA	35			V
BV_{CER}	$I_C = 50$ mA $R_{BE} = 10 \Omega$	60			V
BV_{EBO}	$I_E = 10$ mA	4.0			V
I_{CES}	$V_E = 28$ V			5.0	mA
h_{FE}	$V_{CE} = 5.0$ V $I_C = 1.0$ A	10		100	---
C_{ob}	$V_{CB} = 28$ V $f = 1.0$ MHz			5.0	pF
P_{GE}	$V_{CE} = 20$ V $I_{CQ} = 150$ mA $f = 1.0$ GHz $P_{OUT} = 1.0$ W	10			dB